

ENTERED By RCE FILED ON
11/24/08

Docket No.: 21302/0204309-US0
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Euijoon Yoon et al.

Application No.: 10/596,126

Confirmation No.: 2554

Filed: May 31, 2006

Art Unit: 2813

For: GROWTH METHOD OF NITRIDE
SEMICONDUCTOR LAYER AND LIGHT
EMITTING DEVICE USING THE GROWTH
METHOD

Examiner: Crawford, L. N.

RESPONSE TO FINAL OFFICE ACTION (37 C.F.R. § 1.116)

MS AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Final Office Action dated June 23, 2008, and with the Examiner's approval, please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 6 of this paper.

Remarks/Arguments begin on page 7 of this paper.